

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXFH24N60X

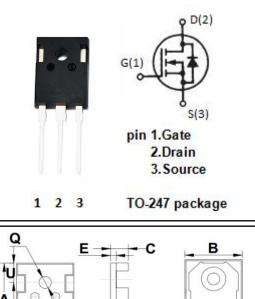
FEATURES

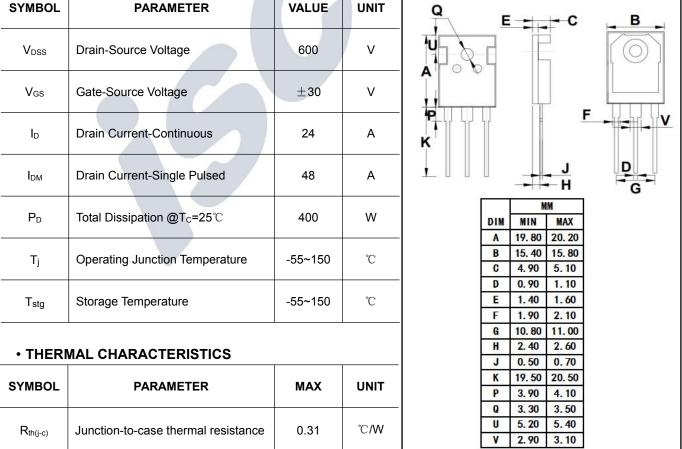
- Static drain-source on-resistance: RDS(on) ≤ 175mΩ@V_{GS}=10V
- · Fully characterized avalanche voltage and current
- 100% Avalanche Tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATION

- · Switched mode power supplies
- DC-DC converters

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V; ID = 250 μ A	600		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} ; ID = 2.5mA	2.5	4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 12A		175	mΩ
I _{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V; V_{DS} =0V		±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V		20	- μ Α
		V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 125°C		750	
Vsd	Diode forward voltage	I _F = 24A; V _{GS} = 0V		1.4	V

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